

Plastic Darlington Complementary Silicon Power Transistors

... designed for general-purpose amplifier and low-speed switching applications.

- High DC Current Gain —
 $h_{FE} = 2000$ (Typ) @ I_C
 $= 2.0$ Adc
- Monolithic Construction with Built-in Base-Emitter Resistors to Limit Leakage Multiplication
- Choice of Packages —
 MJE700 and MJE800 series

MAXIMUM RATINGS

Rating	Symbol	MJE700 MJE800	MJE702 MJE703 MJE802 MJE803	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CB}	60	80	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current	I_C	4.0		Adc
Base Current	I_B	0.1		Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	CASE 77		Watts W/ $^\circ\text{C}$
		40 0.32		
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case CASE 77 TO-220	$R_{\theta JC}$	3.13 2.50	$^\circ\text{C}/\text{W}$

PNP
MJE700
MJE702
MJE703
NPN
MJE800
MJE802
MJE803

4.0 AMPERE
DARLINGTON
POWER TRANSISTORS
COMPLEMENTARY
SILICON
40 WATT
50 WATT

STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. BASE

CASE 77-08
TO-225AA TYPE
MJE700-703
MJE800-803

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

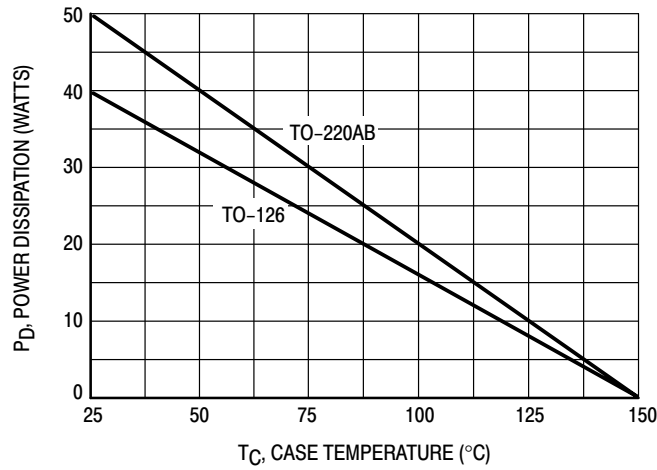


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (1) ($I_C = 50\text{ mAdc}$, $I_B = 0$)	MJE700, MJE800 MJE702, MJE703, MJE802, MJE803	$V_{(BR)CEO}$	60 80	— — Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 80\text{ Vdc}$, $I_B = 0$)	MJE700, MJE800 MJE702, MJE703, MJE802, MJE803	I_{CEO}	— —	100 100 μAdc
Collector Cutoff Current ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$) ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$, $T_C = 100^\circ\text{C}$)		I_{CBO}	— —	100 500 μAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	—	2.0 mAdc
ON CHARACTERISTICS				
DC Current Gain (1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	MJE700, MJE702, MJE800, MJE802 MJE703, MJE803 All devices	h_{FE}	750 750 100	— — —
Collector–Emitter Saturation Voltage (1) ($I_C = 1.5\text{ Adc}$, $I_B = 30\text{ mAdc}$) ($I_C = 2.0\text{ Adc}$, $I_B = 40\text{ mAdc}$) ($I_C = 4.0\text{ Adc}$, $I_B = 40\text{ mAdc}$)	MJE700, MJE702, MJE800, MJE802 MJE703, MJE803 All devices	$V_{CE(sat)}$	— — —	2.5 2.8 3.0 Vdc
Base–Emitter On Voltage (1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	MJE700, MJE702, MJE800, MJE802 MJE703, MJE803 All devices	$V_{BE(on)}$	— — —	2.5 2.5 3.0 Vdc
DYNAMIC CHARACTERISTICS				
Small–Signal Current Gain ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)		h_{fe}	1.0	— —

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

R_B & R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS
 D_1 , MUST BE FAST RECOVERY TYPE, e.g.:
 1N5825 USED ABOVE $I_B \approx 100$ mA
 MSD6100 USED BELOW $I_B \approx 100$ mA

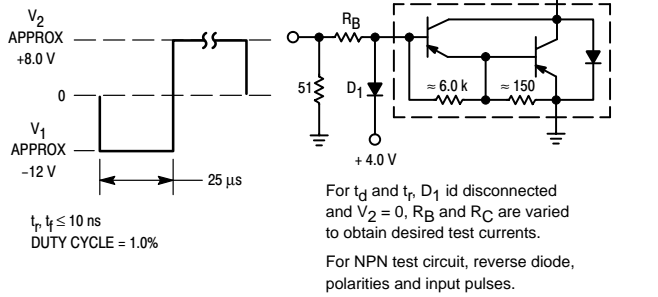


Figure 2. Switching Times Test Circuit

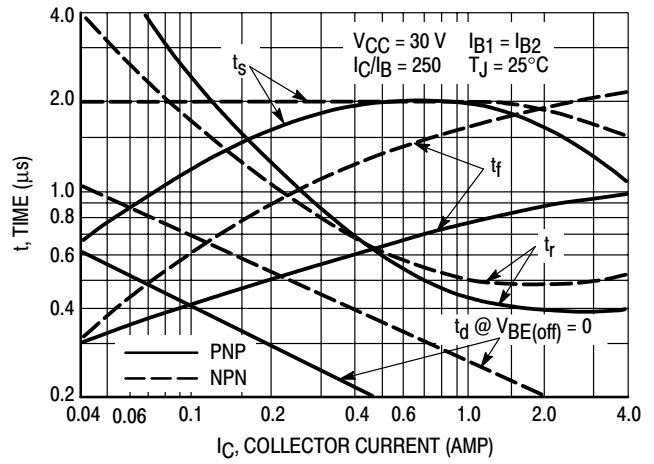


Figure 3. Switching Times

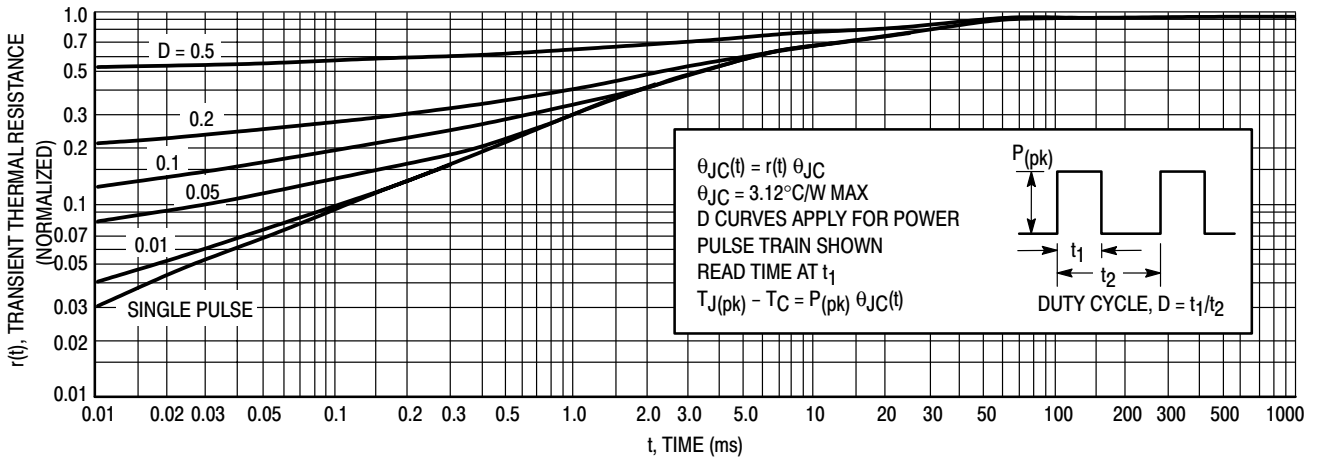


Figure 4. Thermal Response (MJE700, 800 Series)

ACTIVE-REGION SAFE-OPERATING AREA

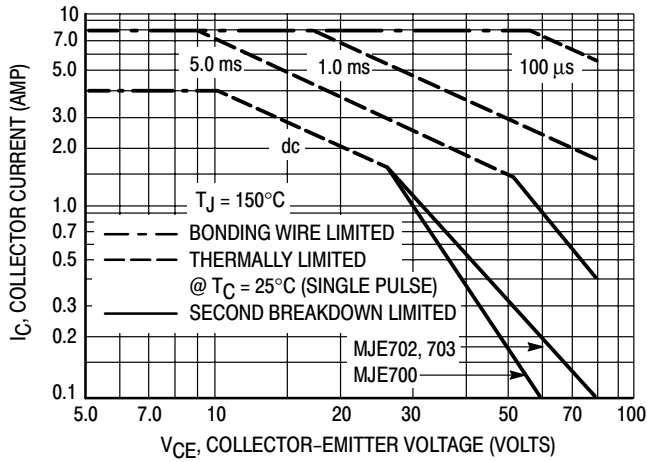


Figure 5. MJE700 Series

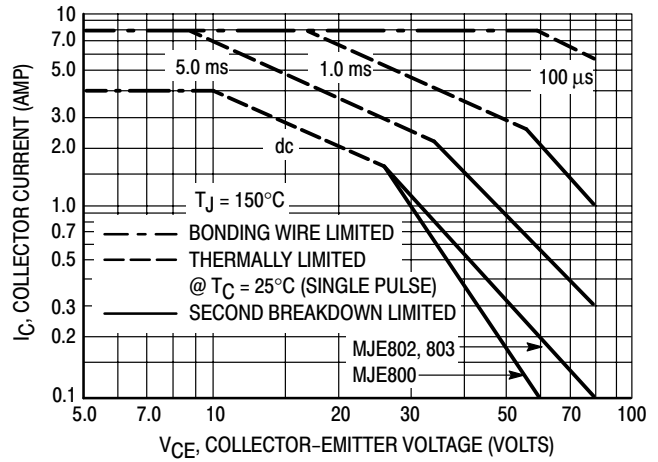


Figure 6. MJE800 Series

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5 and 6 are based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown

pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

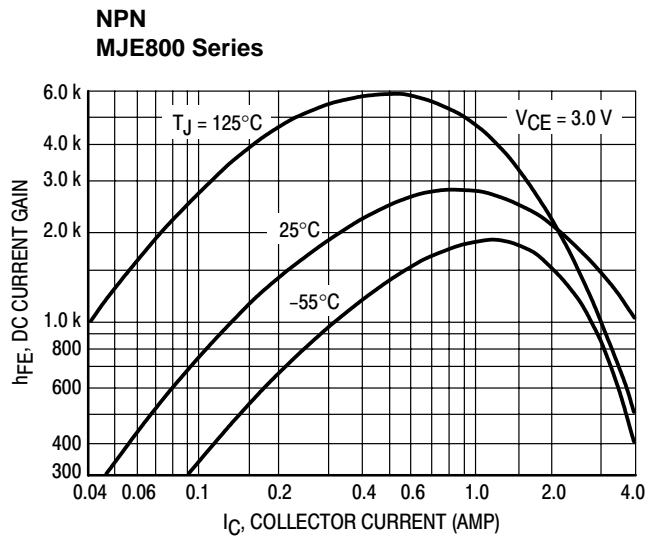
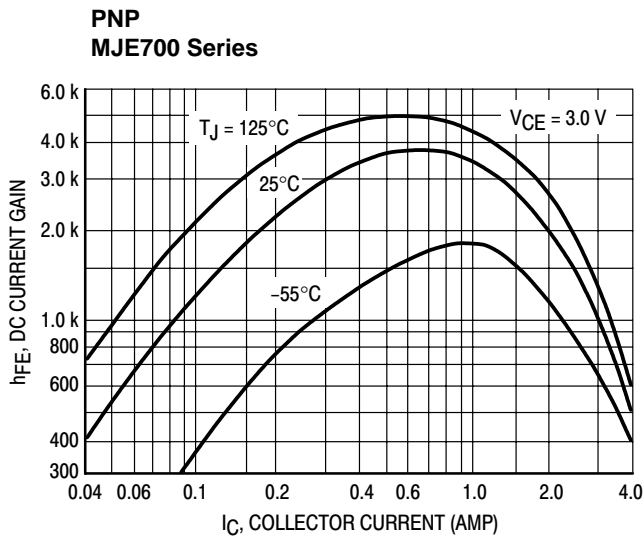


Figure 7. DC Current Gain

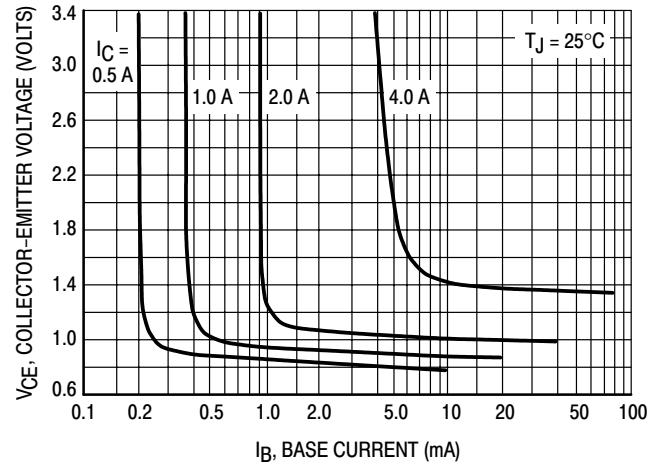
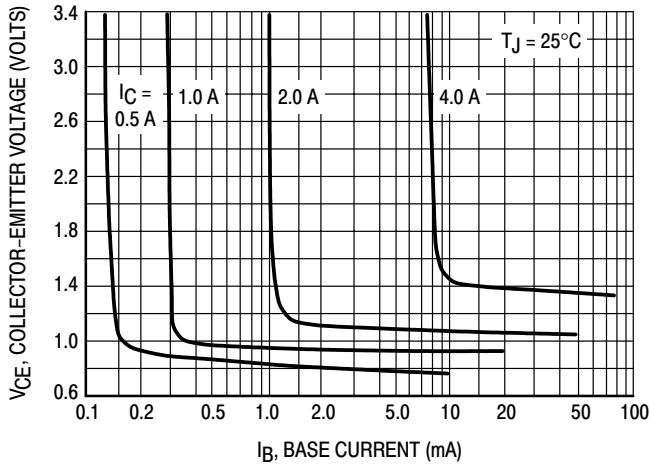


Figure 8. Collector Saturation Region

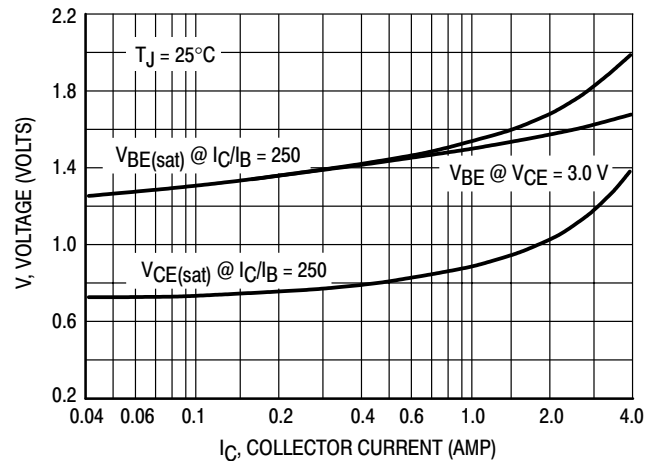
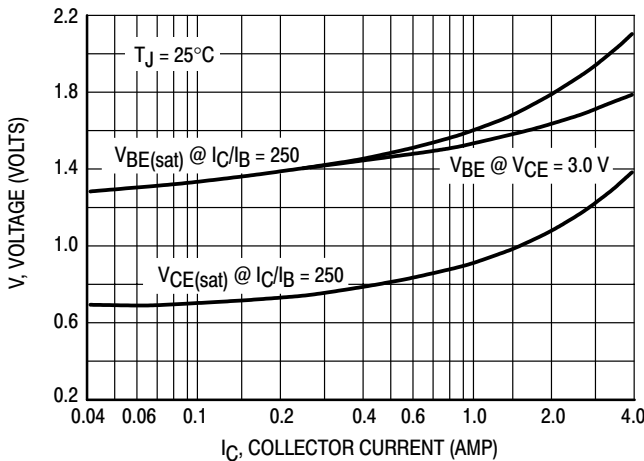
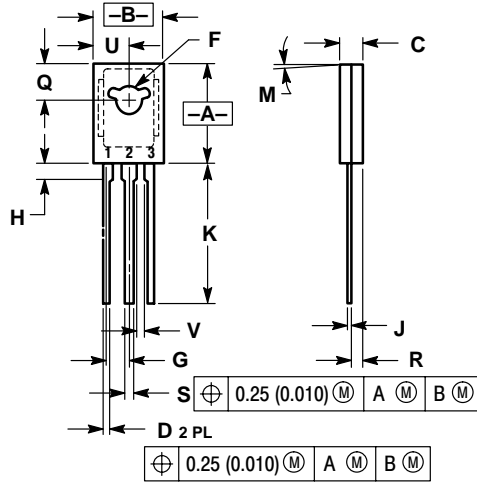


Figure 9. "On" Voltages

MJE700 MJE702 MJE703 MJE800 MJE802 MJE803

PACKAGE DIMENSIONS

TO-225AA
CASE 77-09
ISSUE W




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

- STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

Notes

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